

Docket Number (Optional)	Application Number
SETI-0001	09/966563
Applicant(s)	
Khan et al.	
Filing Date	Group Art Unit
September 27, 2001	2814

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Pb	"The Influence of the Strain-Induced Electric Field on the Charge Distribution in GaN-AlN-GaN Structure," A. D. Bykhovski et al., Journal of Applied Physics, Vol. 74, No. 11, December 1, 1993, pp.6734-6739.
h	"Pyroelectricity in Gallium Nitride Thin Films," A. D. Bykhovski et al., Applied Physics Letters, Vol. 69, No. 21, November 18, 1996, pp. 3254-3256.

DATE CONSIDERED

SHEET 1 OF 2

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

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*EXAMINER

INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

"Pyroelectric and Piezoelectric Properties of GaN-Based Materials," M. S. Shur et al., MRS Internet J. Nitride Semicond. Res. 4S1, G1.6 (1999), pp. 1-12.

"Piezoeffect and Gate Current in AlGaIn/GaN High Electron Mobility Transistors," R. Gaska et al., Applied Physics Letters, Vol. 71, No. 25, December 22, 1997, pp. 3673-3675.

"Two-Dimensional Electron-Gas Density in Al_xGa_{1-x}N/GaN Heterostructure Field-Effect Transistors," N. Maeda et al., Applied Physics Letters, Vol. 73, No. 13, September 28, 1998, pp. 1856-1858.

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"Lattice and Energy Band Engineering in AlInGaIn/GaN Heterostructures," M. A. Khan et al., Applied Physics Letters, Vol. 76, No. 9, February 28, 2000, pp. 1161-1163.

"Electron Mobility in Modulation-Doped AlGaIn-GaN Heterostructures," R. Gaska et al., Applied Physics Letters, Vol. 74, No. 2, January 11, 1999, pp. 287-289.

"High Pinch-off Voltage AlGaIn-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, Charlottesville, VA, December 1997, pp. 377-380.

"Optoelectronic GaN-Based Field Effect Transistors," M. S. Shur et al., SPIE Vol. 2397, pp. 294-303.

"Current/Voltage Characteristic Collapse in AlGaIn/GaN Heterostructure Insulated Gate Field Effect Transistors at High Drain Bias," M. A. Khan et al., Electronic Letters, Vol. 30, No. 25, December 8, 1994, pp. 2175-2176.

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DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.